

74LVC3G17

Triple non-inverting Schmitt trigger with 5 V tolerant input

Rev. 11 — 9 April 2013

Product data sheet

1. General description

The 74LVC3G17 provides three non-inverting buffers with Schmitt trigger input. It is capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of the 74LVC3G17 as a translator in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- ± 24 mA output drive ($V_{CC} = 3.0$ V)
- CMOS low-power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Multiple package options
- Specified from -40 °C to $+85$ °C and -40 °C to $+125$ °C

3. Applications

- Wave and pulse shapers for highly noisy environments



4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC3G17DP	−40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC3G17DC	−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC3G17GT	−40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74LVC3G17GF	−40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm	SOT1089
74LVC3G17GD	−40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; Ubody 3 × 2 × 0.5 mm	SOT996-2
74LVC3G17GM	−40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 × 1.6 × 0.5 mm	SOT902-2
74LVC3G17GN	−40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	SOT1116
74LVC3G17GS	−40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1.0 × 0.35 mm	SOT1203

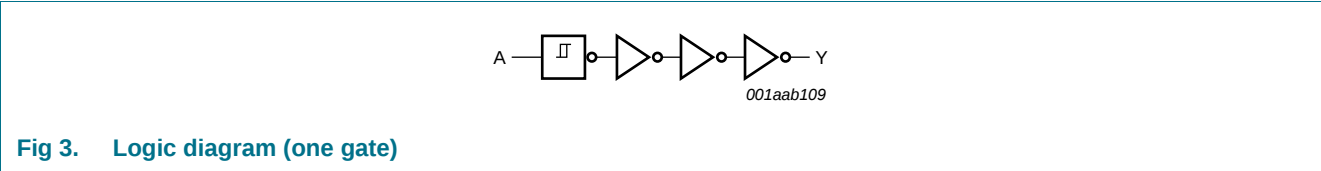
5. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74LVC3G17DP	V17
74LVC3G17DC	V17
74LVC3G17GT	V17
74LVC3G17GF	VV
74LVC3G17GD	V17
74LVC3G17GM	V17
74LVC3G17GN	VV
74LVC3G17GS	VV

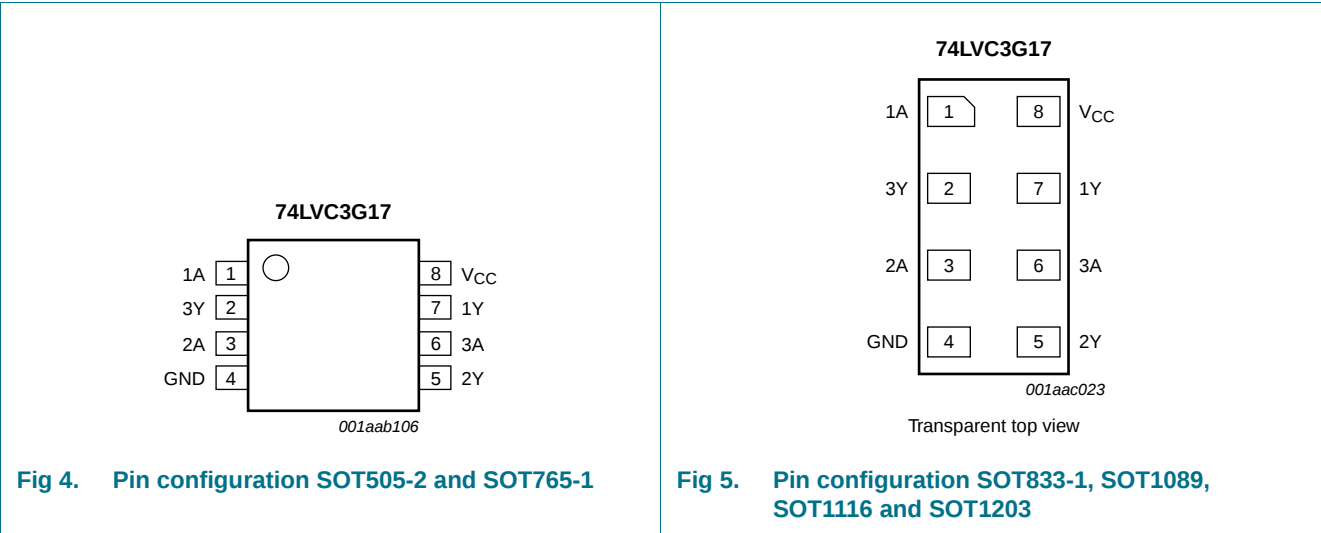
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

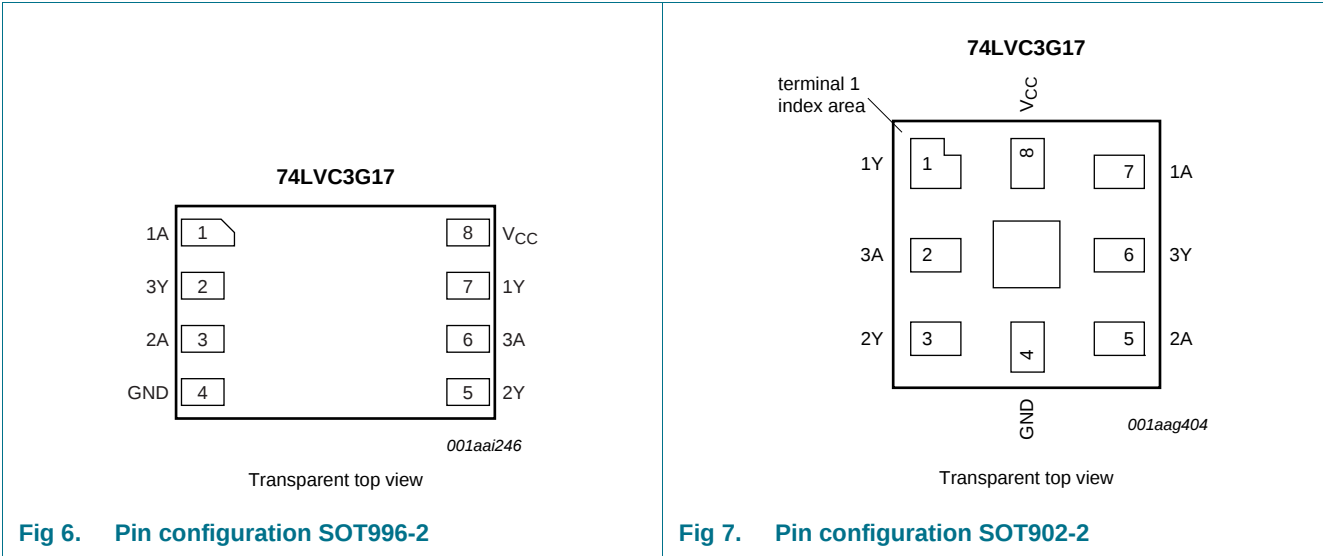
6. Functional diagram



7. Pinning information

7.1 Pinning





7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2	
1A, 2A, 3A	1, 3, 6	7, 5, 2	data input
GND	4	4	ground (0 V)
1Y, 2Y, 3Y	7, 5, 2	1, 3, 6	data output
V _{CC}	8	8	supply voltage

8. Functional description

Table 4. Function table^[1]

Input	Output
nA	nY
L	L
H	H

[1] H = HIGH voltage level; L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		[1] -0.5	+6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	± 50	mA
V_O	output voltage	Active mode	[1] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	[1][2] -0.5	+6.5	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	± 50	mA
I_{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[3] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.65	5.5	V
V_I	input voltage		0	5.5	V
V_O	output voltage		0	V_{CC}	V
T_{amb}	ambient temperature		-40	+125	°C

11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
T_{amb} = -40 °C to +85 °C						
V _{OL}	LOW-level output voltage	V _I = V _{T+} or V _{T-}				
		I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.3	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.4	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.55	V
V _{OH}	HIGH-level output voltage	V _I = V _{T+} or V _{T-}				
		I _O = -100 µA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	1.2	-	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	2.2	-	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.3	-	-	V
		I _O = -32 mA; V _{CC} = 4.5 V	3.8	-	-	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	[2] -	±0.1	±5	µA
I _{OFF}	power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0 V	-	±0.1	±10	µA
I _{CC}	supply current	V _I = 5.5 V or GND; I _O = 0 A; V _{CC} = 1.65 V to 5.5 V	-	0.1	10	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	[2] -	5	500	µA
C _I	input capacitance		-	3.5	-	pF
T_{amb} = -40 °C to +125 °C						
V _{OL}	LOW-level output voltage	V _I = V _{T+} or V _{T-}				
		I _O = 100 µA; V _{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.70	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.60	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.80	V
		I _O = 32 mA; V _{CC} = 4.5 V	-	-	0.80	V
V _{OH}	HIGH-level output voltage	V _I = V _{T+} or V _{T-}				
		I _O = -100 µA; V _{CC} = 1.65 V to 5.5 V	V _{CC} - 0.1	-	-	V
		I _O = -4 mA; V _{CC} = 1.65 V	0.95	-	-	V
		I _O = -8 mA; V _{CC} = 2.3 V	1.7	-	-	V
		I _O = -12 mA; V _{CC} = 2.7 V	1.9	-	-	V
		I _O = -24 mA; V _{CC} = 3.0 V	2.0	-	-	V
		I _O = -32 mA; V _{CC} = 4.5 V	3.4	-	-	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	±20	µA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ ^[1]	Max	Unit
I_{OFF}	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	-	± 20	μ A
I_{CC}	supply current	$V_I = 5.5$ V or GND; $I_O = 0$ A; $V_{CC} = 1.65$ V to 5.5 V	-	-	40	μ A
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	-	5	mA

[1] All typical values are measured at $T_{amb} = 25$ °C.[2] These typical values are measured at $V_{CC} = 3.3$ V.

12. Dynamic characteristics

Table 8. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t_{pd}	propagation delay	nA to nY; see Figure 8 ^[2]						
		$V_{CC} = 1.65$ V to 1.95 V	1.5	5.6	10.5	1.5	13.1	ns
		$V_{CC} = 2.3$ V to 2.7 V	1.0	3.7	6.5	1.0	8.5	ns
		$V_{CC} = 2.7$ V	1.0	3.8	6.5	1.0	8.5	ns
		$V_{CC} = 3.0$ V to 3.6 V	1.0	3.6	5.7	1.0	7.1	ns
		$V_{CC} = 4.5$ V to 5.5 V	1.0	2.7	4.3	1.0	5.4	ns
C_{PD}	power dissipation capacitance	per buffer; $V_{CC} = 3.3$ V; $V_I = \text{GND to } V_{CC}$ ^[3]	-	16.3	-	-	-	pF

[1] Typical values are measured at $T_{amb} = 25$ °C and $V_{CC} = 1.8$ V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.[2] t_{pd} is the same as t_{PLH} and t_{PHL} .[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W). $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where: f_i = input frequency in MHz; f_o = output frequency in MHz; C_L = output load capacitance in pF; V_{CC} = supply voltage in V; N = number of inputs switching; $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

13. Waveforms

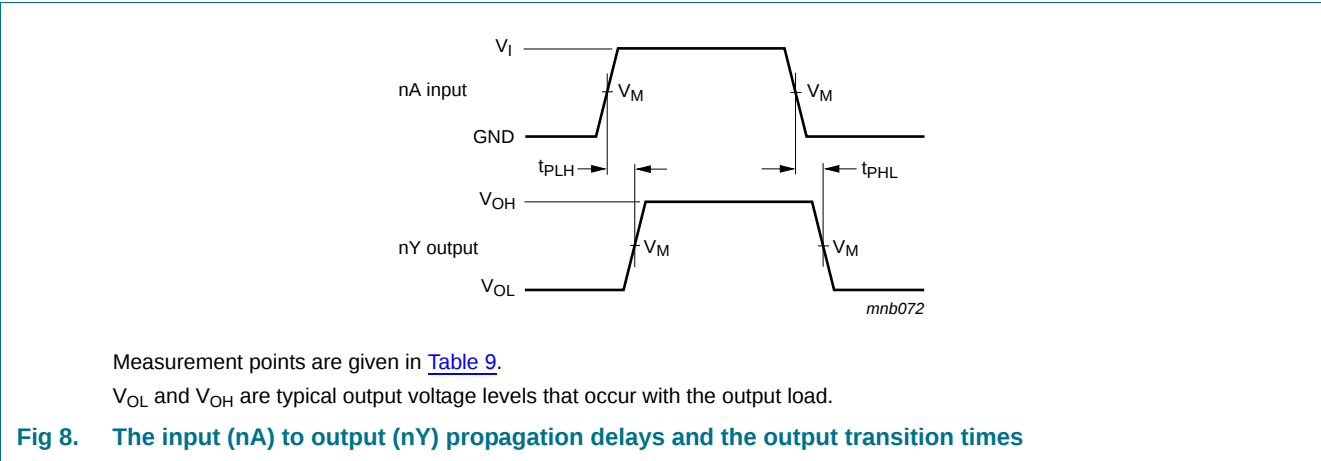
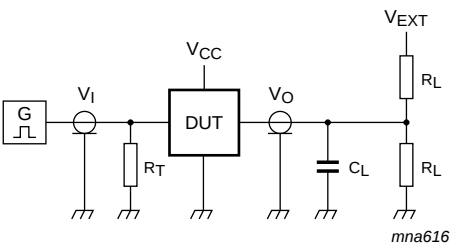


Table 9. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in [Table 10](#).
Definitions for test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.
 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input		Load		V_{EXT}		
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 k Ω	open	GND	$2 \times V_{CC}$
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open	GND	$2 \times V_{CC}$
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open	GND	$2 \times V_{CC}$

14. Transfer characteristics

Table 11. Transfer characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V_{T+}	positive-going threshold voltage	see Figure 10 and Figure 11						
		$V_{CC} = 1.8 \text{ V}$	0.70	1.10	1.50	0.70	1.70	V
		$V_{CC} = 2.3 \text{ V}$	1.00	1.40	1.80	1.00	2.00	V
		$V_{CC} = 3.0 \text{ V}$	1.30	1.76	2.20	1.30	2.40	V
		$V_{CC} = 4.5 \text{ V}$	1.90	2.47	3.10	1.90	3.30	V
		$V_{CC} = 5.5 \text{ V}$	2.20	2.91	3.60	2.20	3.80	V
V_{T-}	negative-going threshold voltage	see Figure 10 and Figure 11						
		$V_{CC} = 1.8 \text{ V}$	0.25	0.61	0.90	0.25	1.10	V
		$V_{CC} = 2.3 \text{ V}$	0.40	0.80	1.15	0.40	1.35	V
		$V_{CC} = 3.0 \text{ V}$	0.60	1.04	1.50	0.60	1.70	V
		$V_{CC} = 4.5 \text{ V}$	1.00	1.55	2.00	1.00	2.20	V
		$V_{CC} = 5.5 \text{ V}$	1.20	1.86	2.30	1.20	2.50	V
V_H	hysteresis voltage ($V_{T+} - V_{T-}$); see Figure 10 , Figure 11 and Figure 12							
		$V_{CC} = 1.8 \text{ V}$	0.15	0.49	1.00	0.15	1.20	V
		$V_{CC} = 2.3 \text{ V}$	0.25	0.60	1.10	0.25	1.30	V
		$V_{CC} = 3.0 \text{ V}$	0.40	0.73	1.20	0.40	1.40	V
		$V_{CC} = 4.5 \text{ V}$	0.60	0.92	1.50	0.60	1.70	V
		$V_{CC} = 5.5 \text{ V}$	0.70	1.02	1.70	0.70	1.90	V

[1] All typical values are measured at $T_{amb} = 25 \text{ °C}$.

15. Waveforms transfer characteristics

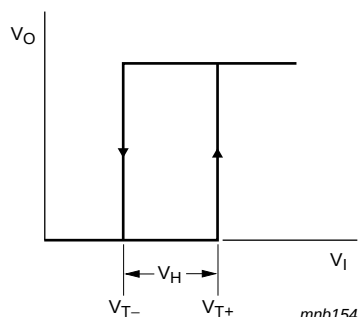
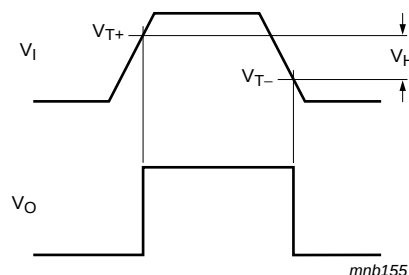
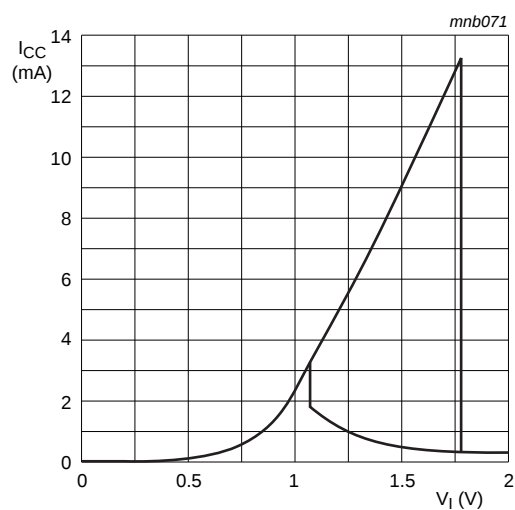


Fig 10. Transfer characteristic



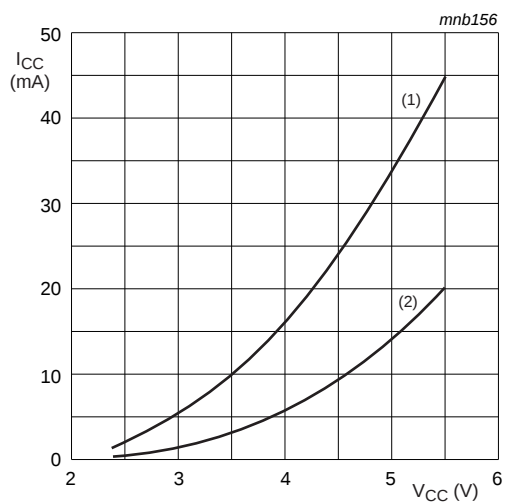
V_{T+} and V_{T-} limits at 70 % and 20 %.

Fig 11. Definition of V_{T+} , V_{T-} and V_H



$V_{CC} = 3.0$ V.

Fig 12. Typical transfer characteristic



- (1) Positive-going edge.
- (2) Negative-going edge.

Linear change of V_I between 0.8 V to 2.0 V. All values given are typical unless otherwise specified.

Fig 13. Average I_{CC} as a function of V_{CC}

16. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

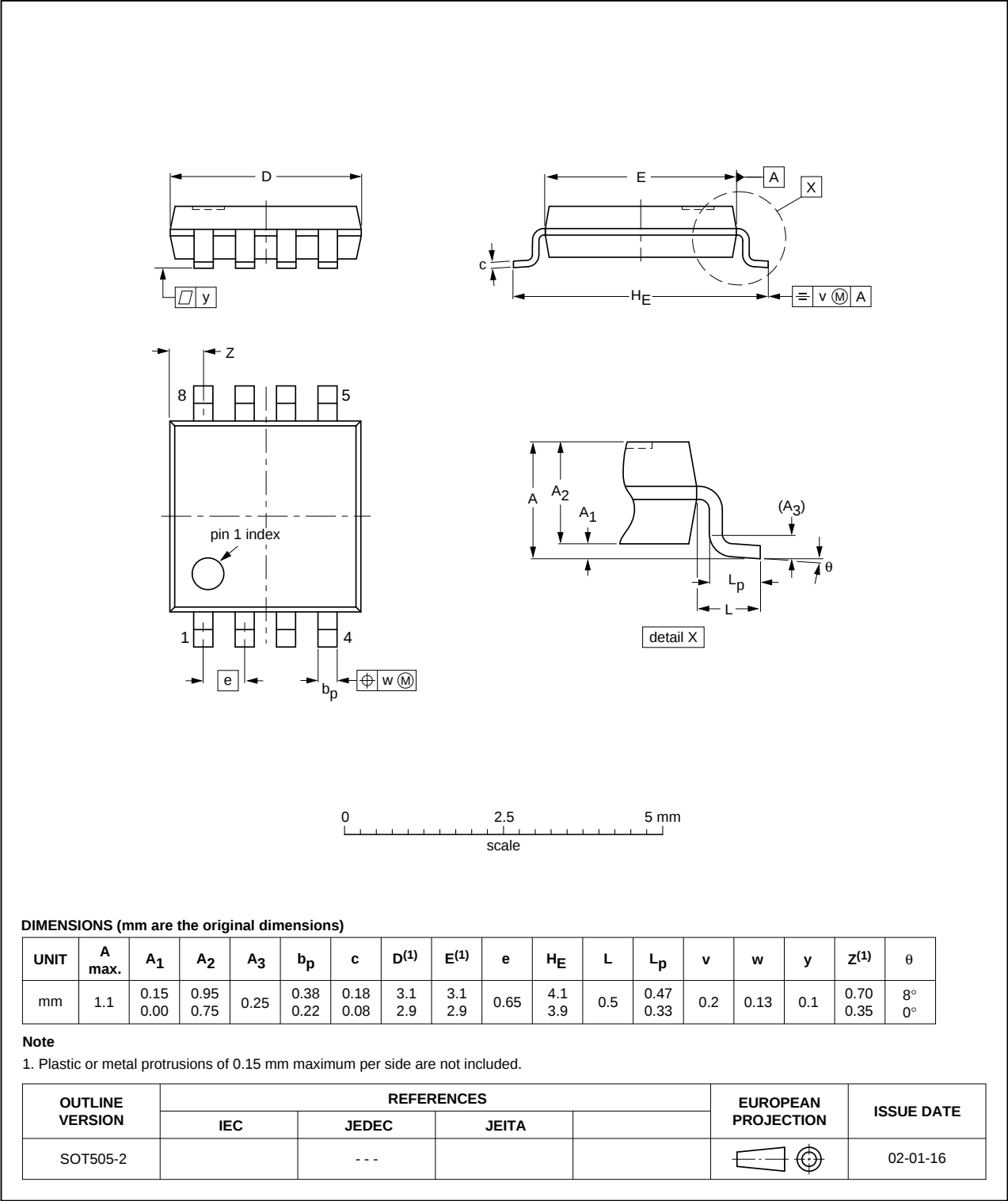


Fig 14. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

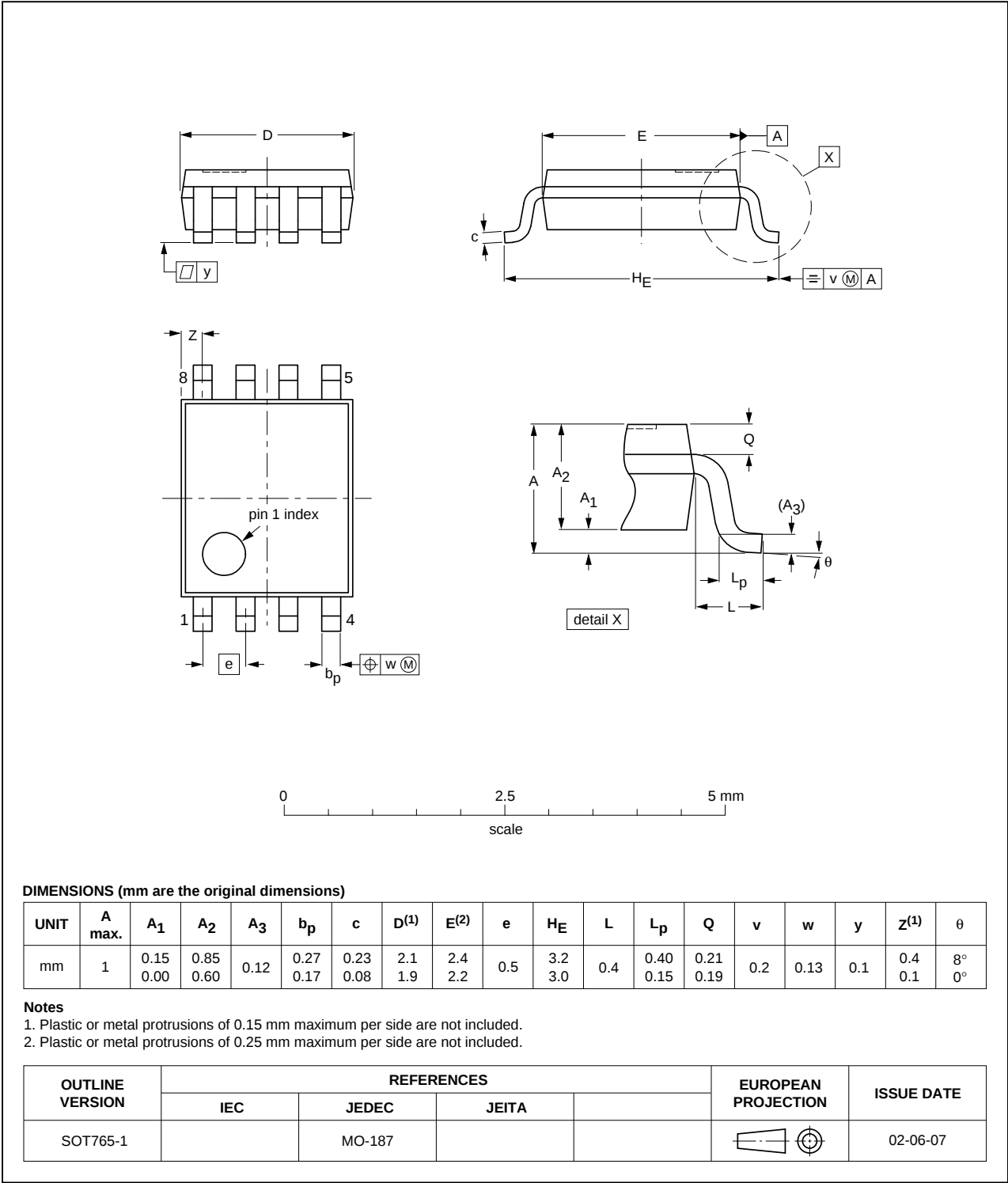


Fig 15. Package outline SOT765-1 (VSSOP8)

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

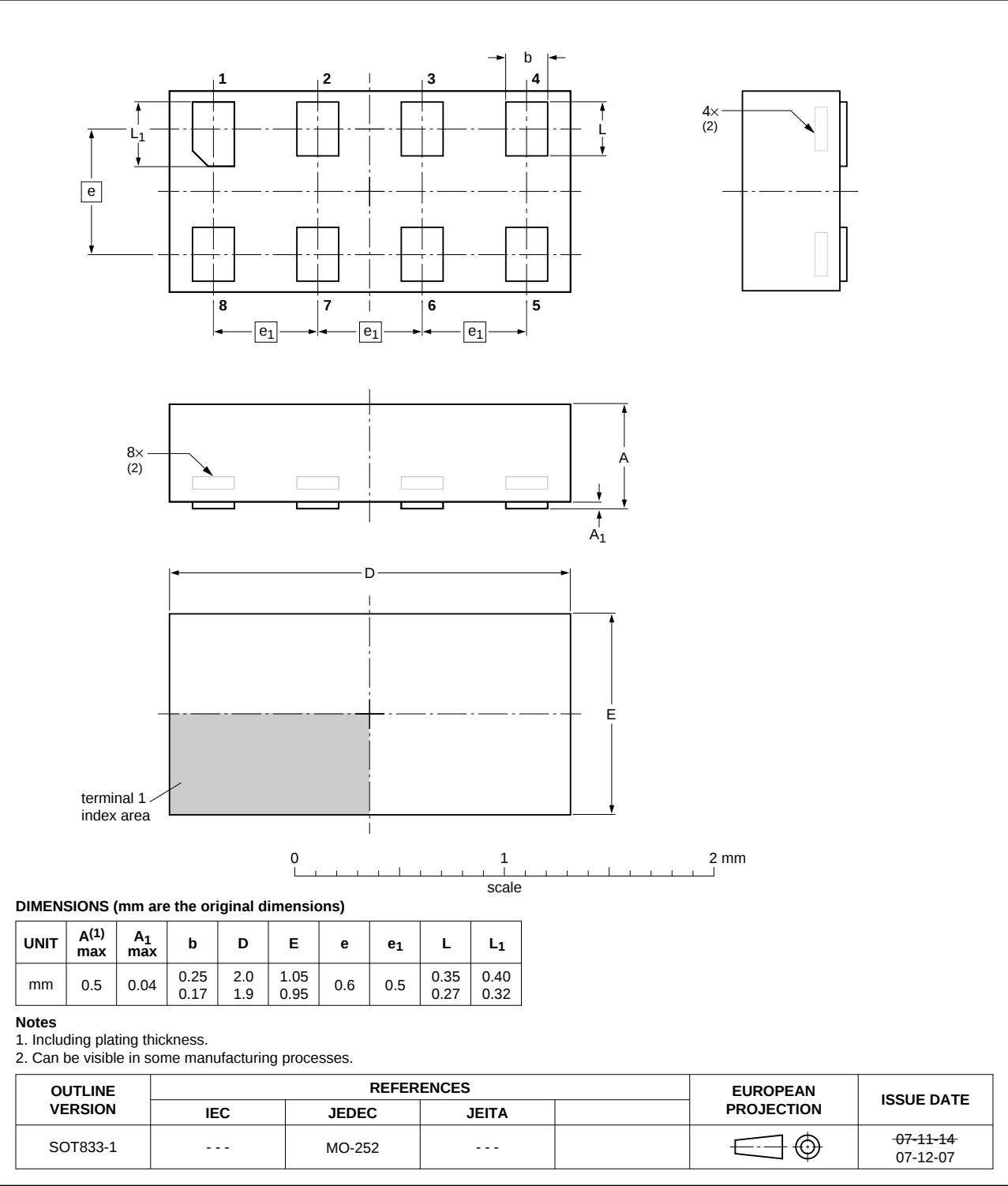
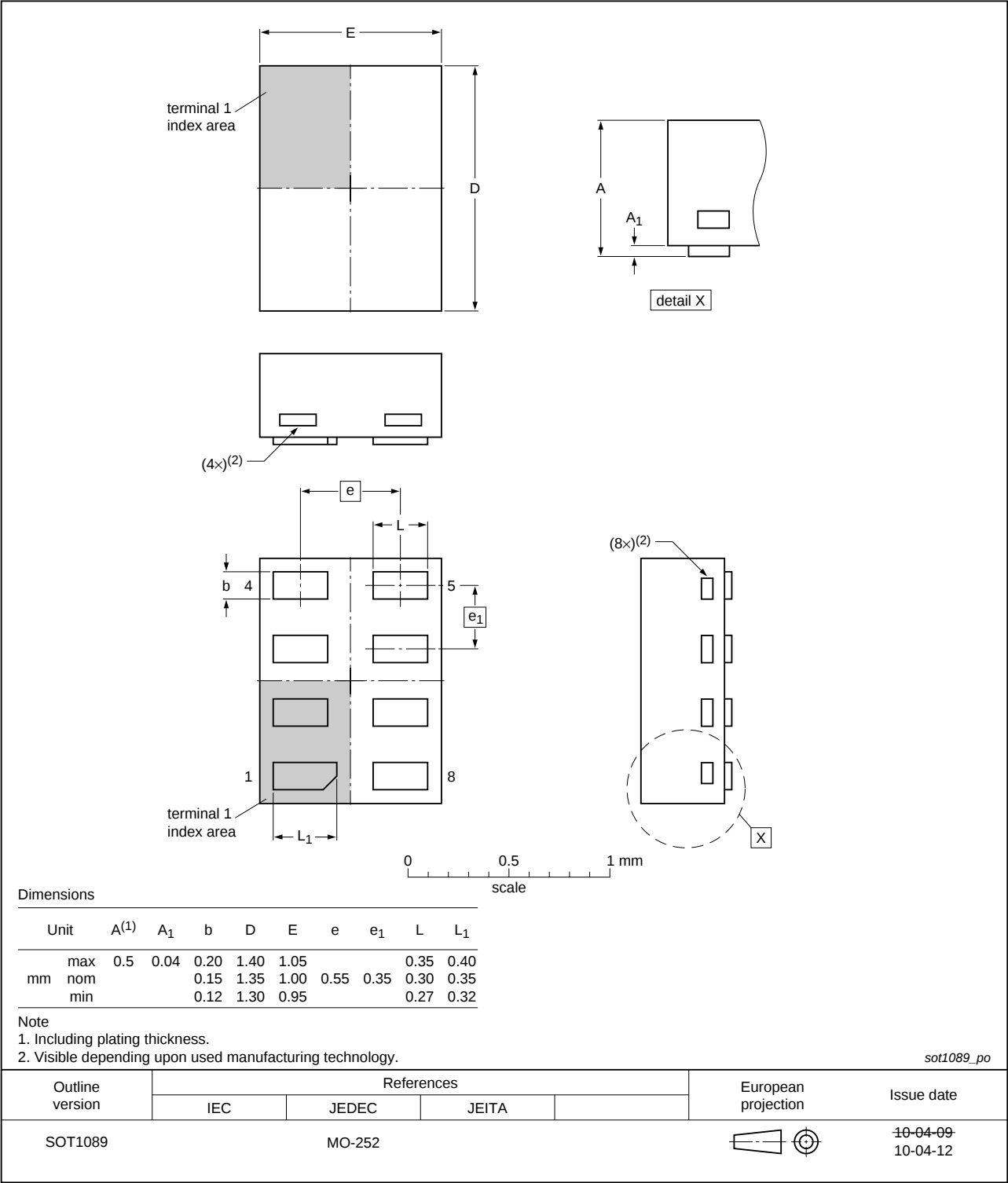


Fig 16. Package outline SOT833-1 (XSON8)

XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.35 x 1 x 0.5 mm

SOT1089



XSON8: plastic extremely thin small outline package; no leads;
8 terminals; body 3 x 2 x 0.5 mm

SOT996-2

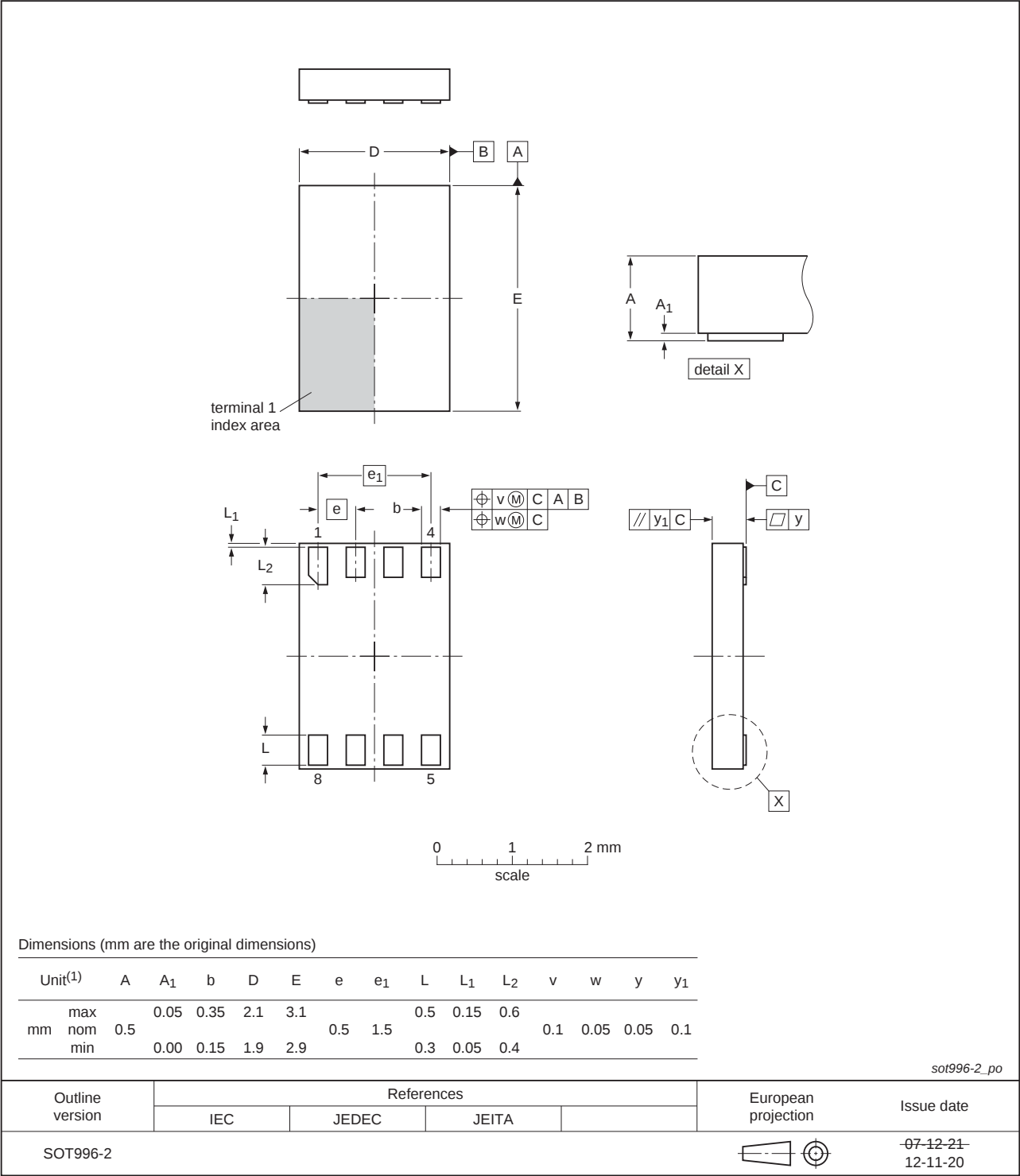


Fig 18. Package outline SOT996-2 (XSON8)

XQFN8: plastic, extremely thin quad flat package; no leads;
8 terminals; body 1.6 x 1.6 x 0.5 mm

SOT902-2

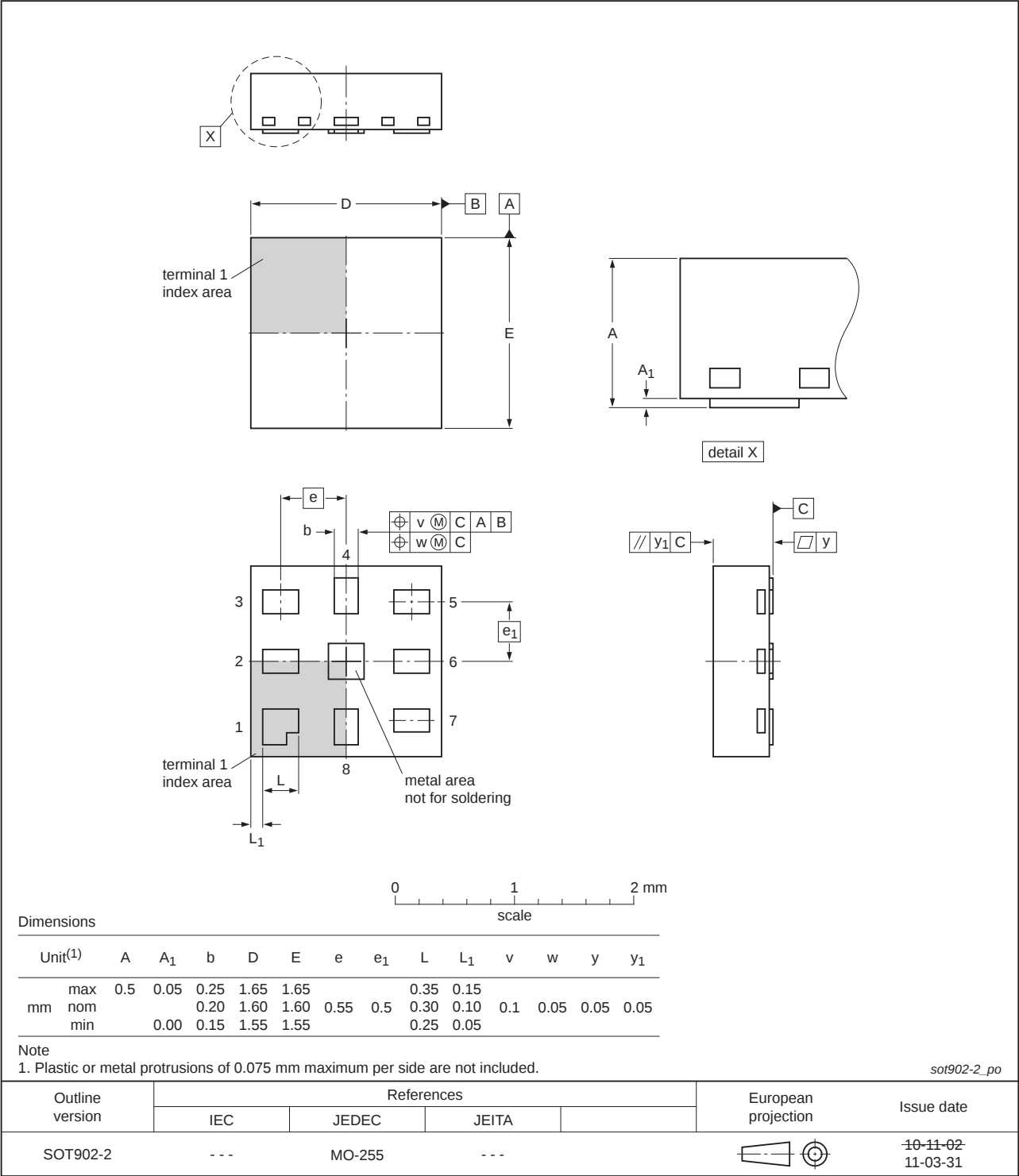


Fig 19. Package outline SOT902-2 (XQFN8)

XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.2 x 1.0 x 0.35 mm

SOT1116

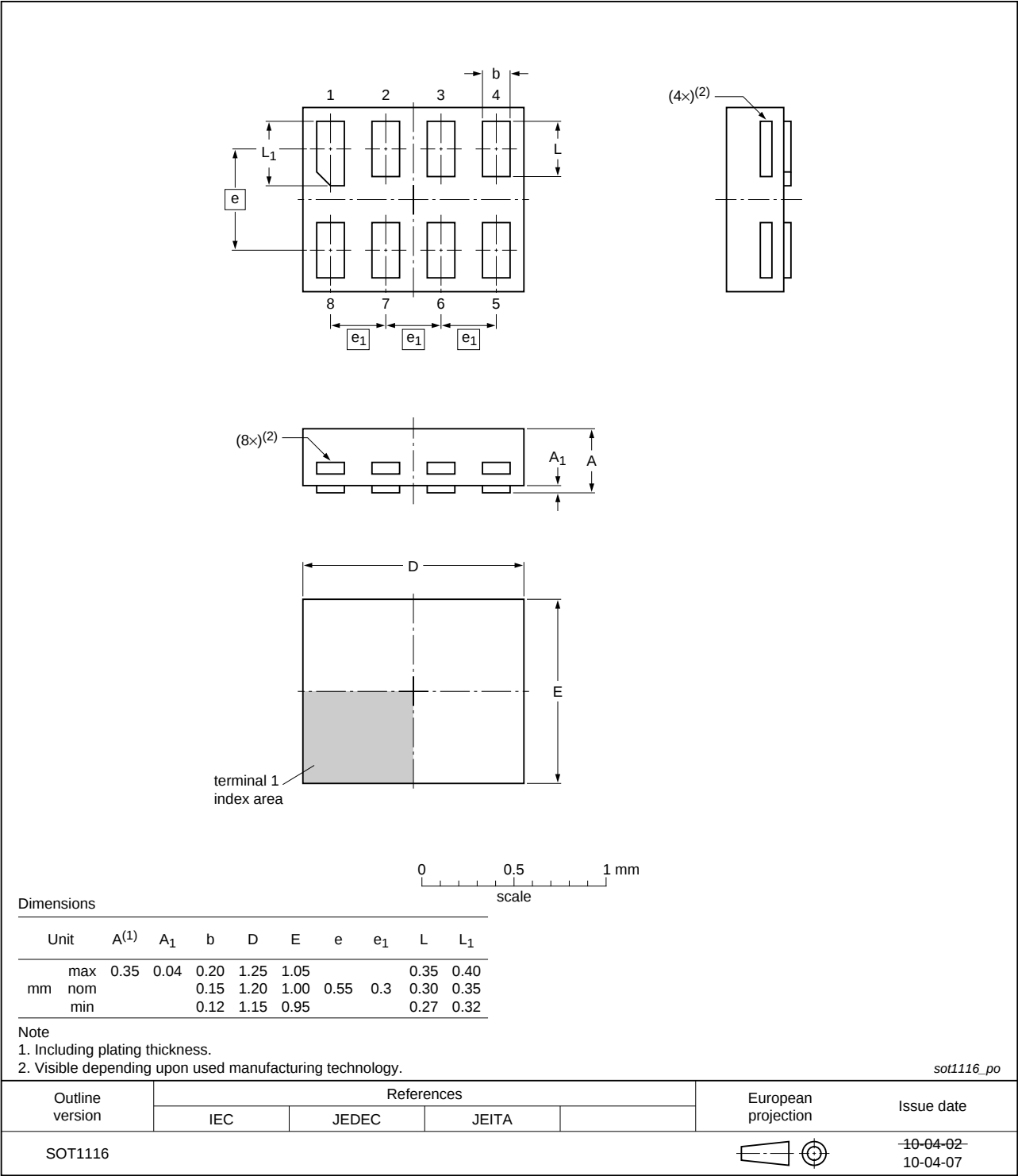


Fig 20. Package outline SOT1116 (XSON8)

XSON8: extremely thin small outline package; no leads;
8 terminals; body 1.35 x 1.0 x 0.35 mm

SOT1203

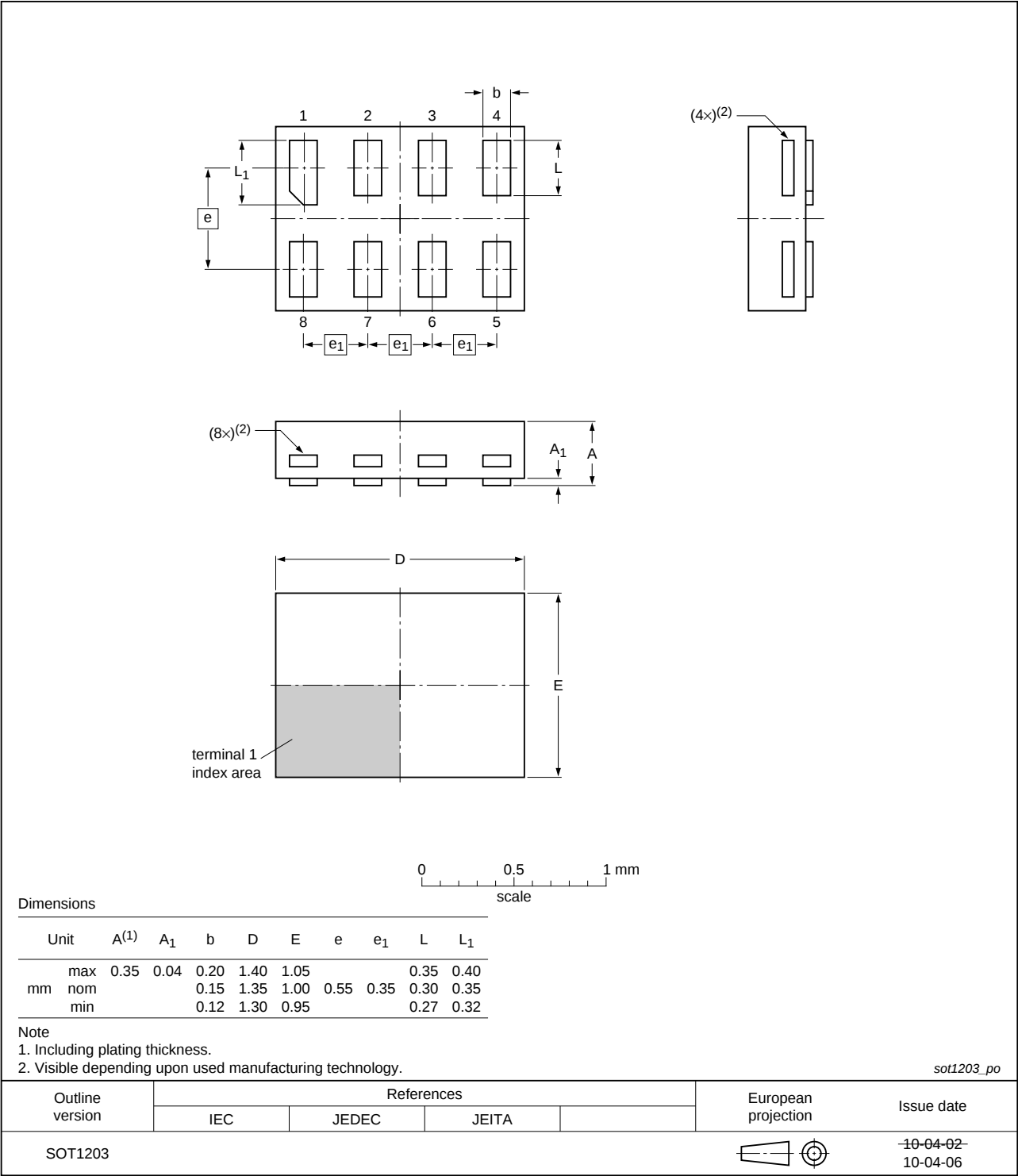


Fig 21. Package outline SOT1203 (XSON8)

17. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

18. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC3G17 v.11	20130409	Product data sheet	-	74LVC3G17 v.10
Modifications:	For type number 74LVC3G17GD XSON8U has changed to XSON8.			
74LVC3G17 v.10	20120706	Product data sheet	-	74LVC3G17 v.9
Modifications:	For type number 74LVC3G17GM the SOT code has changed to SOT902-2.			
74LVC3G17 v.9	20111123	Product data sheet	-	74LVC3G17 v.8
Modifications:	Legal pages updated.			
74LVC3G17 v.8	20110921	Product data sheet	-	74LVC3G17 v.7
74LVC3G17 v.7	20101104	Product data sheet	-	74LVC3G17 v.6
74LVC3G17 v.6	20080606	Product data sheet	-	74LVC3G17 v.5
74LVC3G17 v.5	20080313	Product data sheet	-	74LVC3G17 v.4
74LVC3G17 v.4	20070521	Product data sheet	-	74LVC3G17 v.3
74LVC3G17 v.3	20050131	Product data sheet	-	74LVC3G17 v.2
74LVC3G17 v.2	20041103	Product specification	-	74LVC3G17 v.1
74LVC3G17 v.1	20040624	Product specification	-	-

19. Legal information

19.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

19.2 Definitions

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